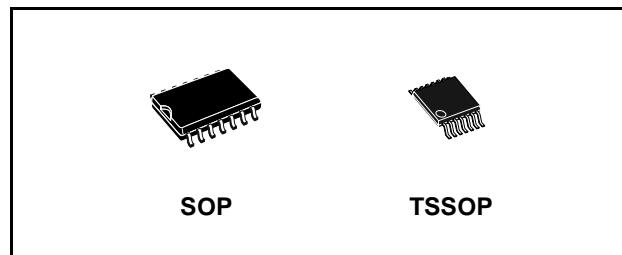


## LOW VOLTAGE CMOS QUAD 2-INPUT OR GATE

- HIGH SPEED:  
 $t_{PD} = 5.2 \text{ ns (TYP.)}$  at  $V_{CC} = 3.3 \text{ V}$
- COMPATIBLE WITH TTL OUTPUTS
- LOW POWER DISSIPATION:  
 $I_{CC} = 2\mu\text{A (MAX.)}$  at  $T_A=25^\circ\text{C}$
- LOW NOISE:  
 $V_{OLP} = 0.3\text{V (TYP.)}$  at  $V_{CC} = 3.3\text{V}$
- $75\Omega$  TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OHL}| = I_{OL} = 12\text{mA (MIN)}$  at  $V_{CC} = 3.0\text{V}$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:  
 $V_{CC(\text{OPR})} = 2\text{V to } 3.6\text{V}$  (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 32
- IMPROVED LATCH-UP IMMUNITY

### DESCRIPTION

The 74LVQ32 is a low voltage CMOS QUAD 2-INPUT OR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS



**Table 1: Order Codes**

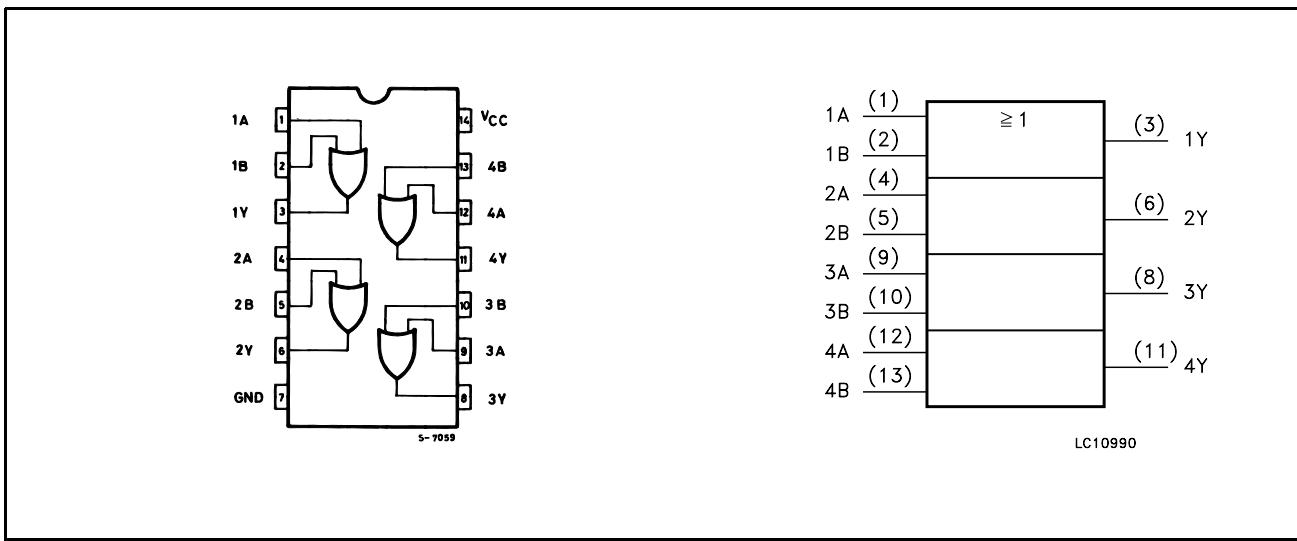
PACKAGE	T & R
SOP	74LVQ32MTR
TSSOP	74LVQ32TTR

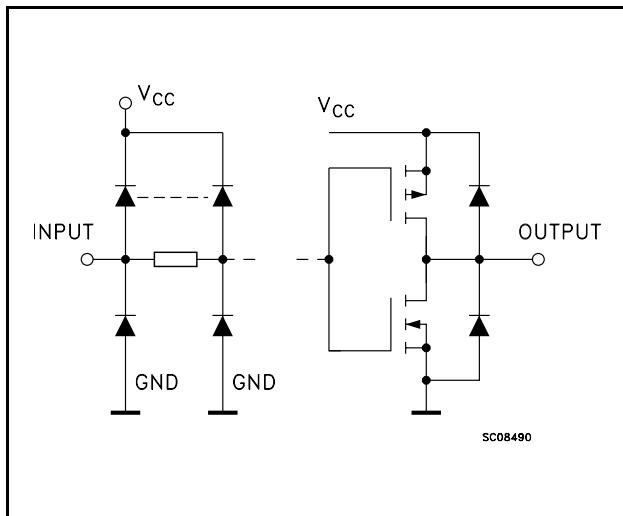
technology. It is ideal for low power and low noise 3.3V applications.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

**Figure 1: Pin Connection And IEC Logic Symbols**



**Figure 2: Input And Output Equivalent Circuit****Table 2: Pin Description**

PIN N°	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

**Table 3: Truth Table**

A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

**Table 4: Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 50	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 200	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

**Table 5: Recommended Operating Conditions**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage (note 1)	2 to 3.6	V
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time V <sub>CC</sub> = 3.0V (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

2) V<sub>IN</sub> from 0.8V to 2V

**Table 6: DC Specifications**

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	3.0 to 3.6		2.0			2.0		2.0		V
V <sub>IL</sub>	Low Level Input Voltage					0.8		0.8		0.8	V
V <sub>OH</sub>	High Level Output Voltage	3.0	I <sub>O</sub> =-50 µA	2.9	2.99		2.9		2.9		V
			I <sub>O</sub> =-12 mA	2.58			2.48		2.48		
			I <sub>O</sub> =-24 mA				2.2		2.2		
V <sub>OL</sub>	Low Level Output Voltage	3.0	I <sub>O</sub> =50 µA		0.002	0.1		0.1		0.1	V
			I <sub>O</sub> =12 mA		0	0.36		0.44		0.44	
			I <sub>O</sub> =24 mA					0.55		0.55	
I <sub>I</sub>	Input Leakage Current	3.6	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	µA
I <sub>CC</sub>	Quiescent Supply Current	3.6	V <sub>I</sub> = V <sub>CC</sub> or GND			2		20		20	µA
I <sub>OLD</sub>	Dynamic Output Current (note 1, 2)	3.6	V <sub>OLD</sub> = 0.8 V max				36		25		mA
I <sub>OHD</sub>			V <sub>OHD</sub> = 2 V min				-25		-25		mA

1) Maximum test duration 2ms, one output loaded at time

2) Incident wave switching is guaranteed on transmission lines with impedances as low as 75Ω

**Table 7: Dynamic Switching Characteristics**

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V <sub>OLP</sub>	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C <sub>L</sub> = 50 pF		0.3	0.8					V
V <sub>OLV</sub>				-0.8	-0.3						
V <sub>IHD</sub>	Dynamic High Voltage Input (note 1, 3)	3.3		2							V
V <sub>ILD</sub>	Dynamic Low Voltage Input (note 1, 3)	3.3				0.8					V

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V<sub>ILD</sub>), 0V to threshold (V<sub>IHD</sub>), f=1MHz.

**Table 8: AC Electrical Characteristics ( $C_L = 50 \text{ pF}$ ,  $R_L = 500 \Omega$ , Input  $t_r = t_f = 3\text{ns}$ )**

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time	2.7		.	5.8	11.0		13.0		14.0	ns
		3.3(*)			5.2	8.0		9.0		10.0	
t <sub>OSLH</sub> t <sub>OSHL</sub>	Output To Output Skew Time (note1, 2)	2.7			0.5	1.0		1.0		1.0	ns
		3.3(*)			0.5	1.0		1.0		1.0	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ( $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$ ,  $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$ )

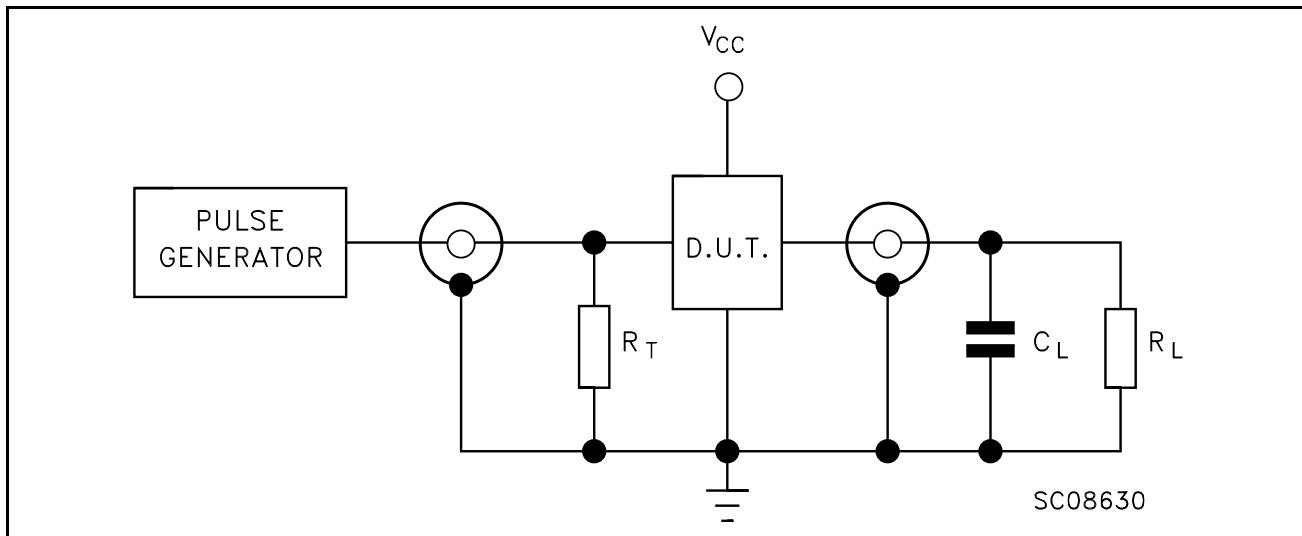
2) Parameter guaranteed by design

(\*) Voltage range is  $3.3V \pm 0.3V$

**Table 9: Capacitive Characteristics**

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance	3.3			4						pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	3.3	f <sub>IN</sub> = 10MHz		26						pF

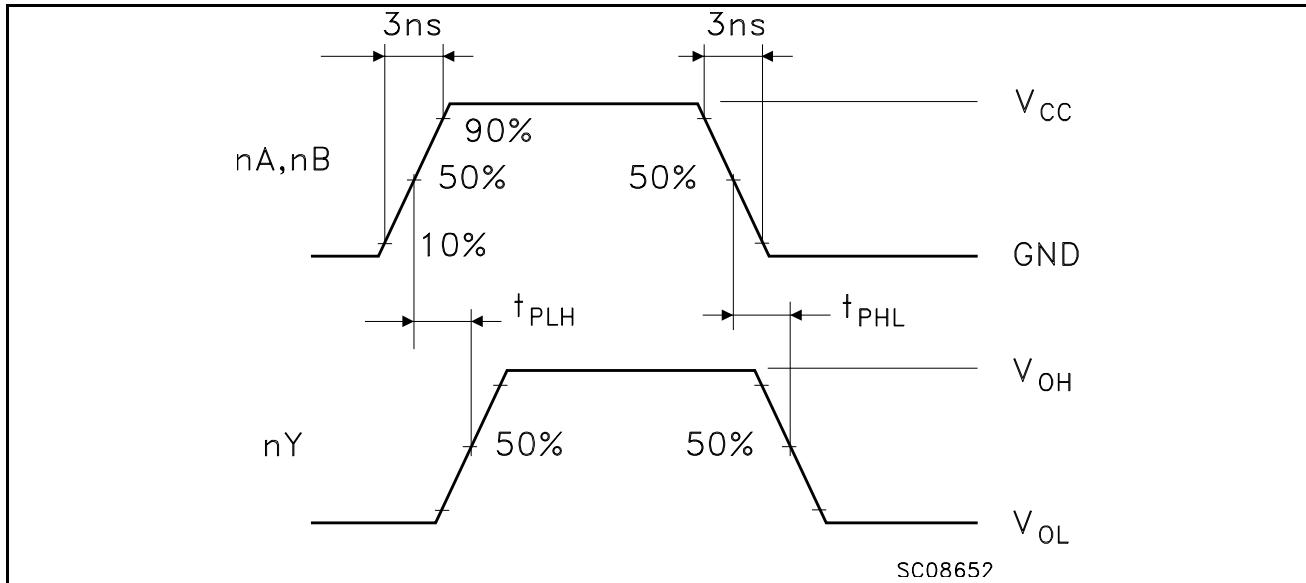
1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> x V<sub>CC</sub> x f<sub>IN</sub> + I<sub>CC</sub>/4 (per gate)

**Figure 3: Test Circuit**

C<sub>L</sub> = 50pF or equivalent (includes jig and probe capacitance)

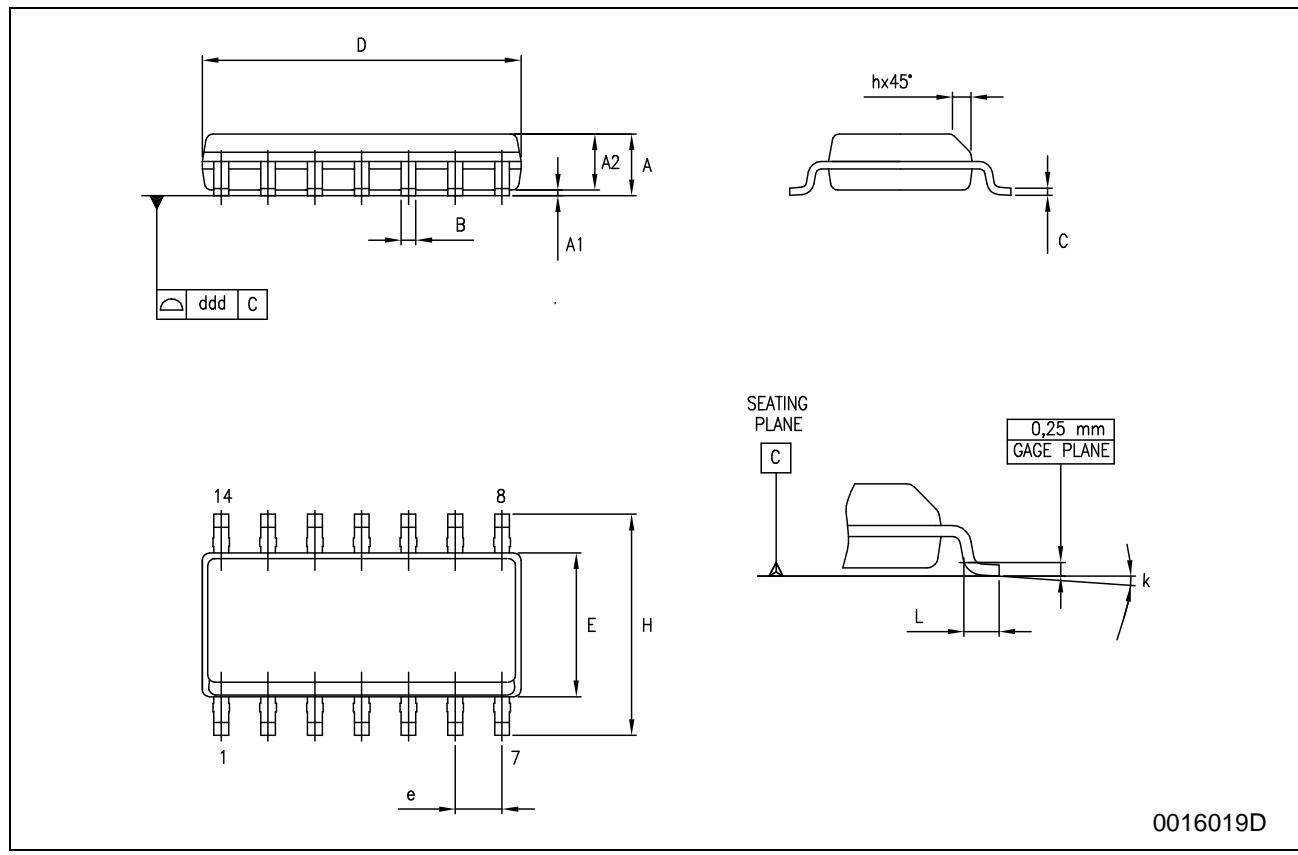
R<sub>L</sub> = 500Ω or equivalent

R<sub>T</sub> = Z<sub>OUT</sub> of pulse generator (typically 50Ω)

**Figure 4: Waveform - Propagation Delays (f=1MHz; 50% duty cycle)**

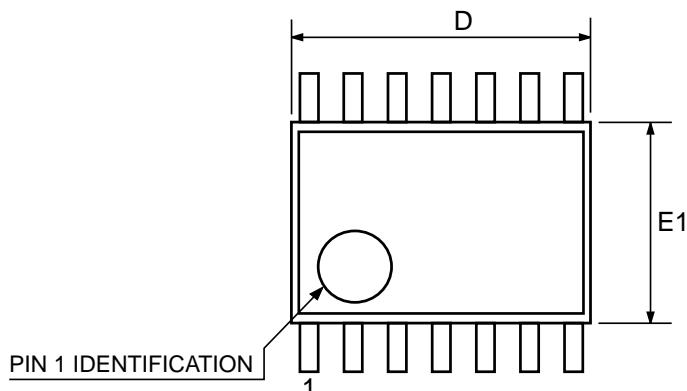
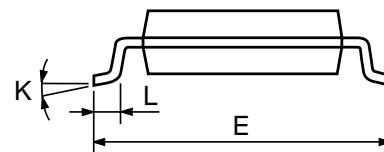
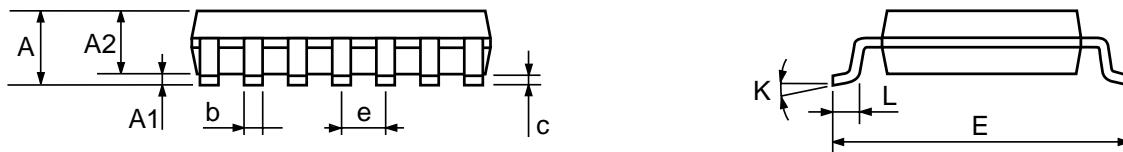
### SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.35		1.75	0.053		0.069
A1	0.1		0.25	0.004		0.010
A2	1.10		1.65	0.043		0.065
B	0.33		0.51	0.013		0.020
C	0.19		0.25	0.007		0.010
D	8.55		8.75	0.337		0.344
E	3.8		4.0	0.150		0.157
e		1.27			0.050	
H	5.8		6.2	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.4		1.27	0.016		0.050
k	0°		8°	0°		8°
ddd			0.100			0.004



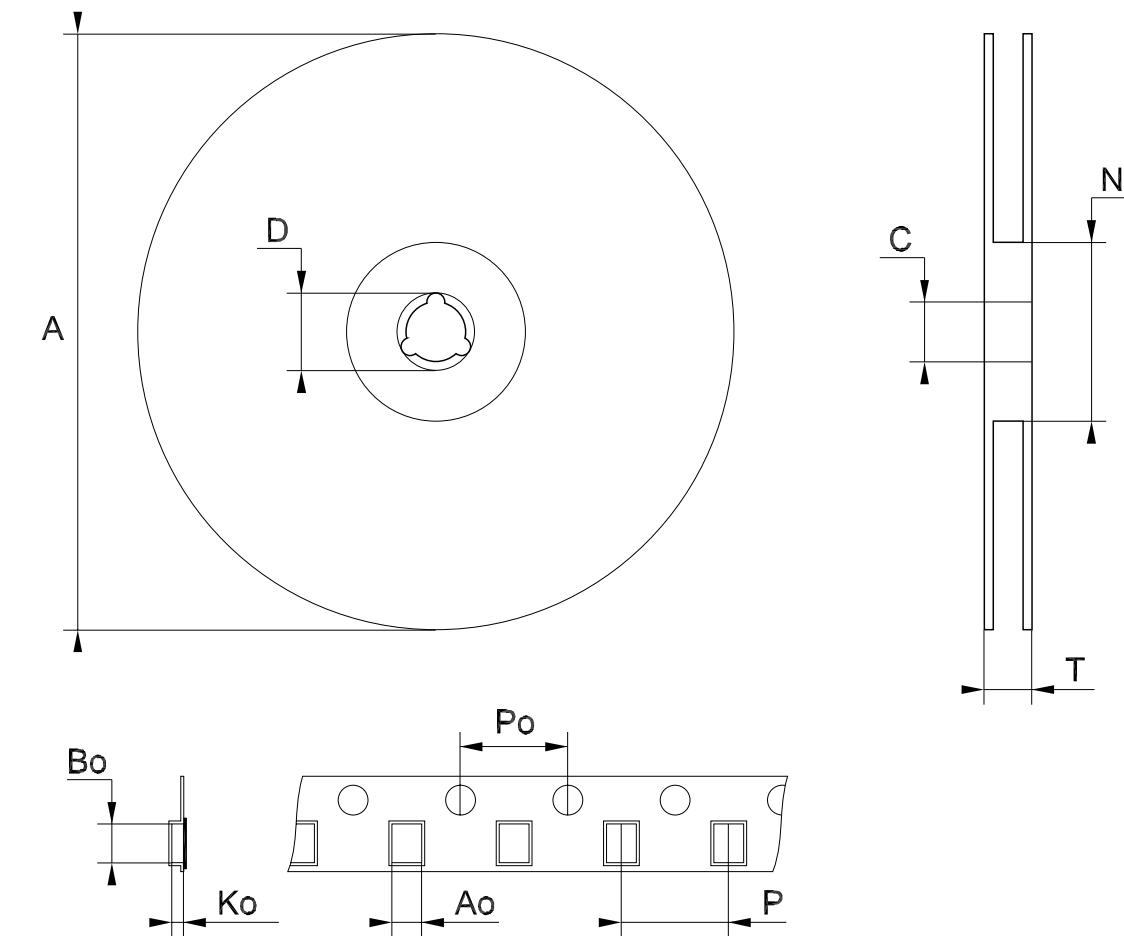
## TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



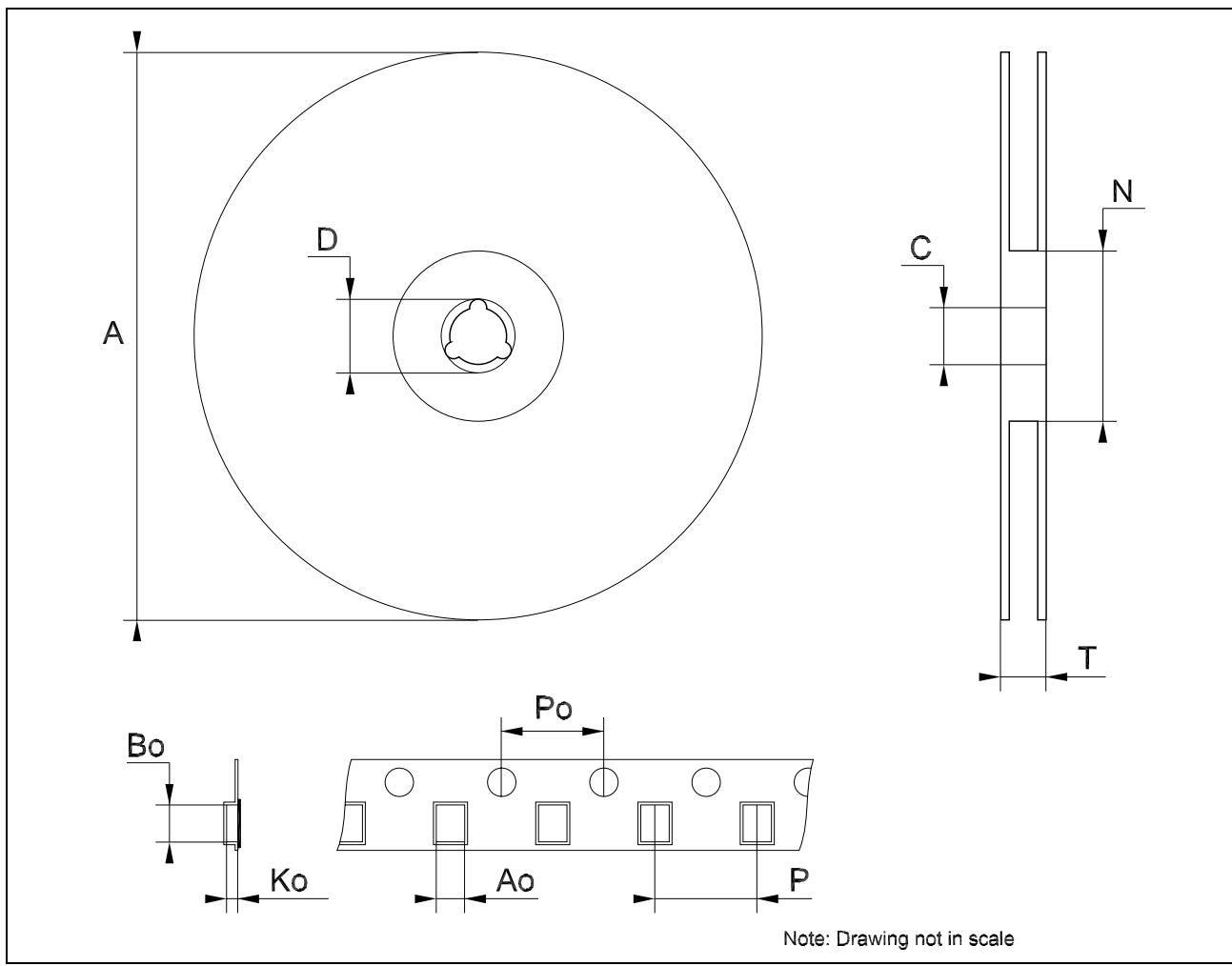
0080337D

Tape & Reel SO-14 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.4		6.6	0.252		0.260
Bo	9		9.2	0.354		0.362
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



Note: Drawing not in scale

Tape & Reel TSSOP14 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Bo	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



**Table 10: Revision History**

Date	Revision	Description of Changes
29-Jul-2004	5	Ordering Codes Revision - pag. 1.

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